CE65H110DNDI

CoreGaN 650V GaN HEMT

Description

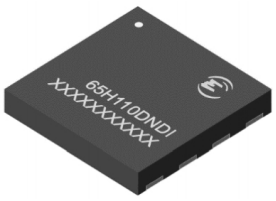
The CE65H110DNDI Series 650V, 110mΩ gallium nitride (GaN) FETs are normally-off devices.

Corenergy GaN FETs offer better efficiency through lower gate charge, faster switching speeds, and lower dynamic on-resistance, delivering significant advantages over traditional silicon (Si) devices.

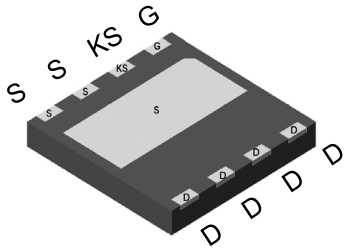
Corenergy is a leading-edge wide band gap supplier with world-class innovation .

Ordering Information

Part Number	Package	Package Configuration
CE65H110DNDI	DFN 8*8	Source



Top



Bottom

Application

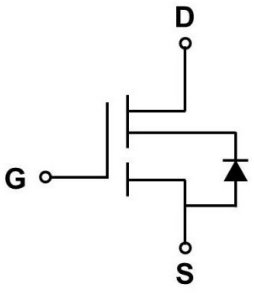
- Adapter
- Renewable energy
- Telecom and data-com
- Servo motors
- Industrial
- Automotive

General Features

Easy to drive—compatible with standard gate drivers

Low conduction and switching losses

RoHS compliant and Halogen-free



Circuit Symbol

Benefits

Increased efficiency through fast switching

Increased power density

Reduced system size and weight

Features

BV_{DSS}	R_{DSON}	I_{DS}	Q_G
650V	110mΩ	18A	6.9nC

CE65H110DNDI

Absolute Maximum Ratings

T_c=25°C unless otherwise stated

Symbol	Parameter		Limit value	Unit
V_{DSS}	Drain to source voltage (T_J = -55°C to 150°C)		650	V
$V_{(TR)DSS}$	Drain to source voltage-transient [a]		800	
V_{GSS}	Gate to source voltage		-20~+20	
I_D	Continuous drain current @T_C=25°C [b]		18	A
	Continuous drain current @T_C=125°C [b]		8	
I_{DM}	Pulse drain current (pulse width: 10μs)		35	A
P_D	Maximum power dissipation @ T_C=25°C		89	W
T_C	Operating temperature	Case	-55~150	°C
T_J		Junction	-55~150	°C
T_S	Storage temperature		-55~150	°C

a. In off-state, spike duty cycle D<0.01, spike duration <1μs

b. For increased stability at high current operation

Thermal Resistance

Symbol	Parameter	Limit value	Unit
$R_{\theta JC}$	Junction-to-case	1.4	°C /W

CE65H110DNDI

Electrical Parameters

T_j=25°C unless otherwise stated

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
Forward Device Characteristics						
$V_{(BL)DSS}$	Drain-source voltage	650	-	-	V	V_{GS}= 0V
$V_{GS(th)}$	Gate threshold voltage	3.3	3.9	4.5	V	V_{DS}=1V, I_{DS}=1mA
$\triangle V_{GS(th)}/T_J$	Gate threshold voltage temperature coefficient	-	-7	-	mV/°C	
$R_{DS(on)}$	Drain-source on-resistance	-	110	145	mΩ	V_{GS}=10V, I_D=6A, T_J=25°C
		-	230	-		V_{GS}=10V, I_D=6A, T_J=150°C
I_{DSS}	Drain-to-source leakage current	-	1	10	μA	V_{DS}=650V, V_{GS}= 0V, T_J=25°C
		-	5	100		V_{DS}=650V, V_{GS}= 0V, T_J=150°C
I_{GSS}	Gate-to-source forward leakage current	-	-	±100	nA	V_{GS}=±20V
C_{ISS}	Input capacitance	-	330	-	pF	V_{GS}=0V, V_{DS}=400V, f=1MHz
C_{OSS}	Output capacitance	-	33	-		
C_{RSS}	Reverse capacitance	-	1.6	-		
Q_G	Total gate charge	-	6.9	-	nC	V_{DS}=400V, V_{GS}=0V to 10V, I_D=1A
Q_{GS}	Gate-source charge	-	2	-		
Q_{GD}	Gate-drain charge	-	3	-		
Q_{OSS}	Output charge	-	48	-	nC	V_{GS}=0V, V_{DS}=0V to 400V, f=1MHz
$t_{D(on)}$	Turn-on delay	-	6.3	-	ns	V_{DS}=400V, V_{GS}=0V to 10V, I_D=2.1A, $R_{G-on(ext)}$=6.8Ω, $R_{G-off(ext)}$=2.2Ω, L=250μH
t_R	Rise time	-	4.1	-		
$t_{D(off)}$	Turn-off delay	-	16.2	-		
t_F	Fall time	-	24.1	-		

Electrical Parameters

T_j=25°C unless otherwise stated

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
Reverse Device Characteristics						
V_{SD}	Source-Drain reverse voltage	-	2.1	-	V	V_{GS}=0V, I_S=10A
t_{RR}	Reverse recovery time	-	14	-	ns	I_s=10A, V_{DD}=400V, di/dt=165A/μs
Q_{RR}	Reverse recovery charge	-	6.5	-	nC	

Typical Characteristics

T_j=25°C unless otherwise stated

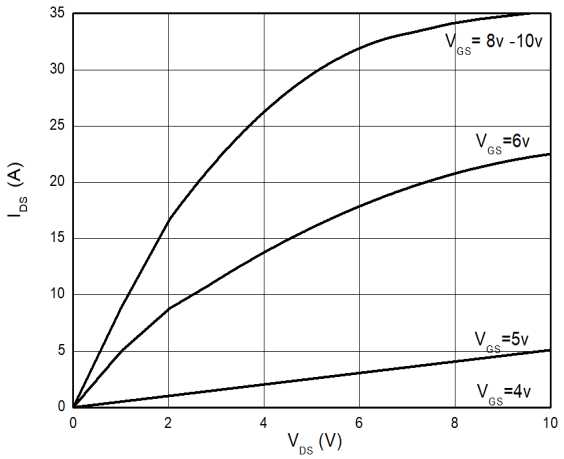


Figure 1. Typical Output Characteristics T_J=25°C

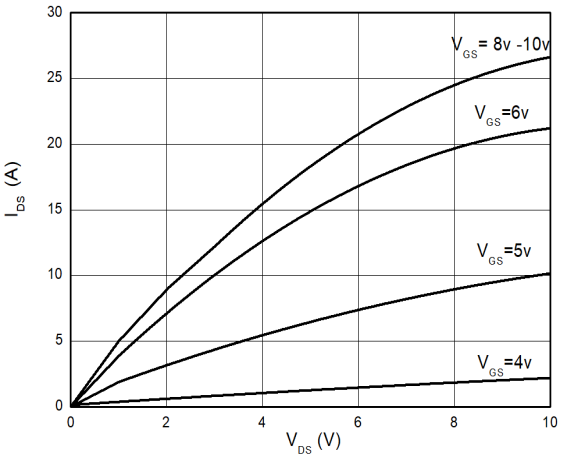


Figure 2. Typical Output Characteristics T_J=125°C

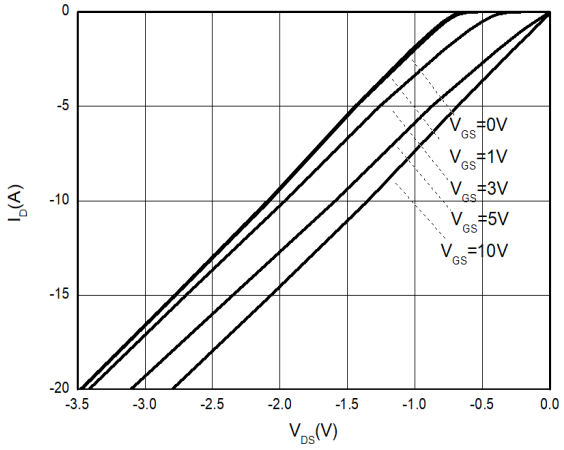


Figure 3. Channel Reverse Characteristics T_J=25°C

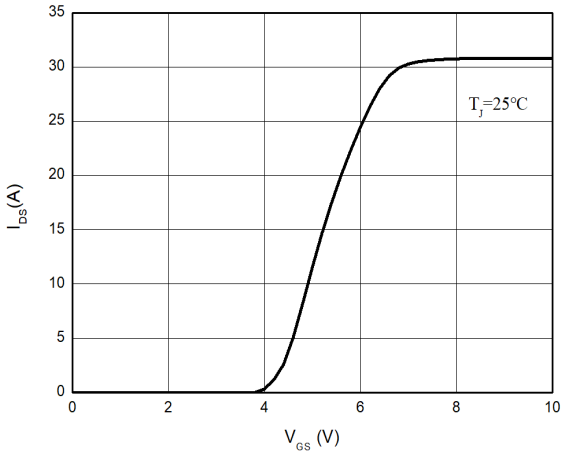


Figure 4. Typical Transfer Characteristics (V_{DS}=10V)

Typical Characteristics

T_j=25°C unless otherwise stated

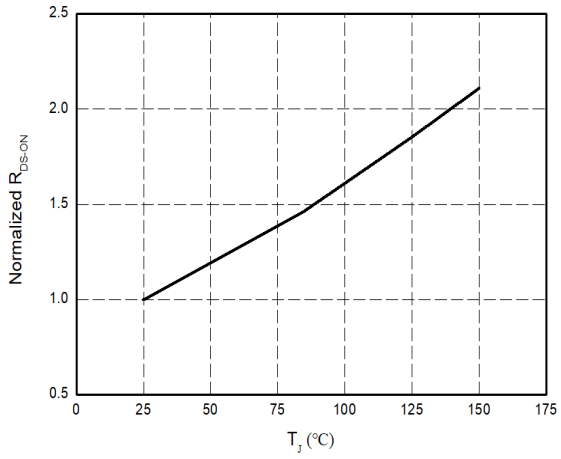


Figure 5. Normalized On-resistance

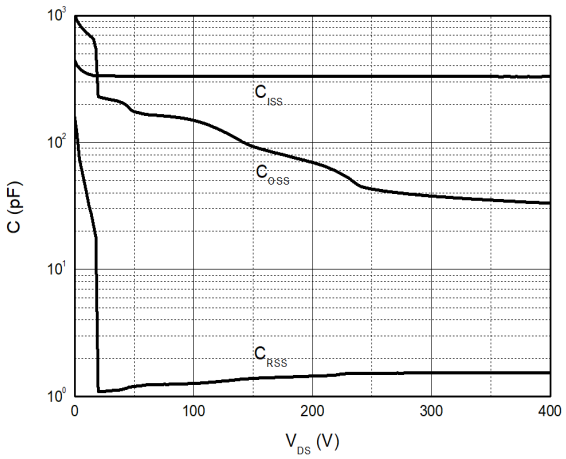


Figure 6. Typical Capacitance (f=1MHz)

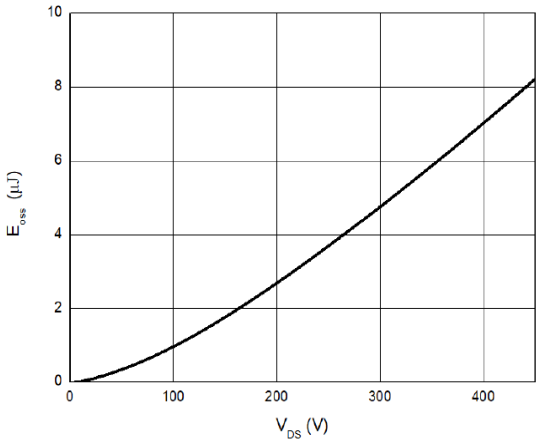


Figure 7. Typical C_{OSS} Stored Energy

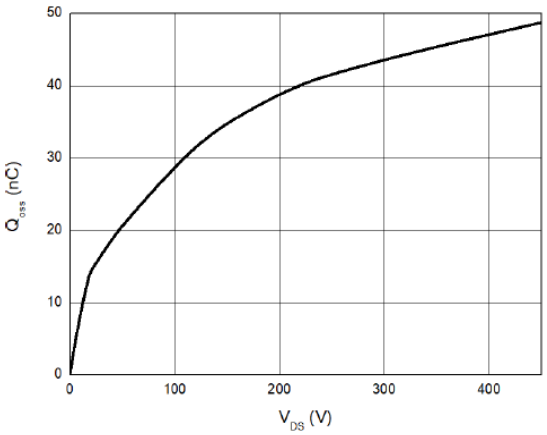


Figure 8. Typical Q_{OSS}

Typical Characteristics

T_j=25°C unless otherwise stated

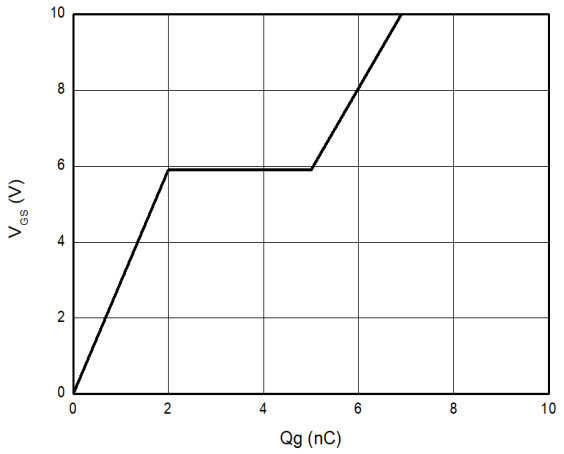


Figure 9. Typical Gate Charge (V_{DS}=400V, I_D=1A)

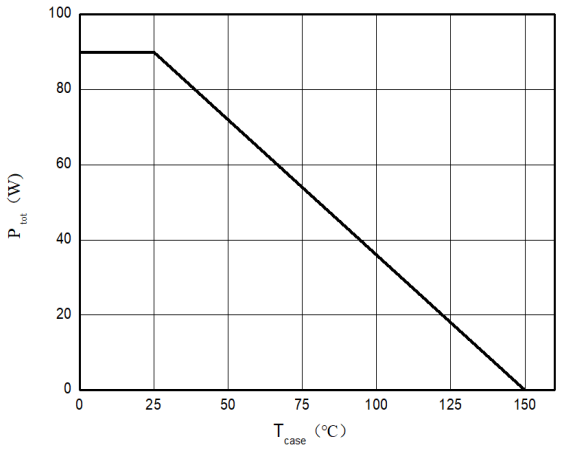


Figure 10. Power Dissipation

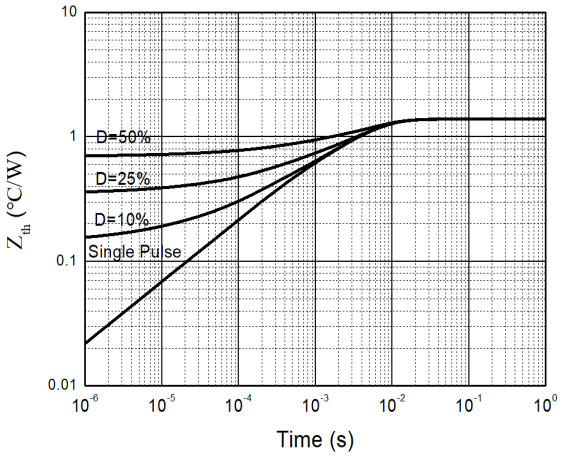


Figure 11. Transient Thermal Resistance

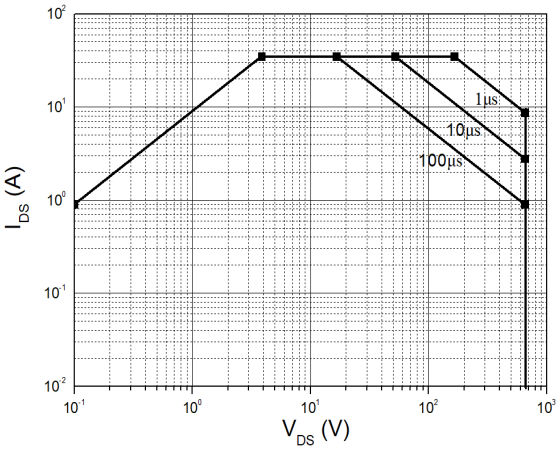


Figure 12. Safe Operating Area T_J=25°C

Typical Characteristics

T_j=25°C unless otherwise stated

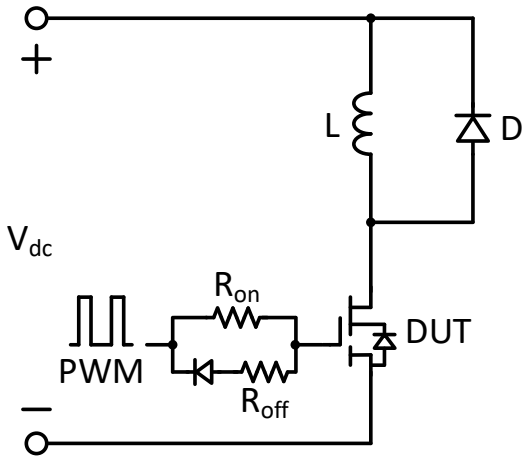


Figure 13. Switching times with inductive load

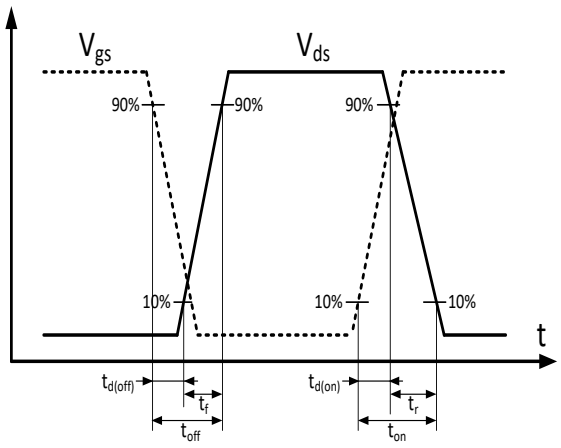


Figure 14. Switching times with waveform

V_{DS}=400V, V_{GS}=0V to 10V, I_D=2.1A,
$R_{G\text{-}on(ext)}$=6.8Ω, $R_{G\text{-}off(ext)}$=2.2Ω, L=250μH

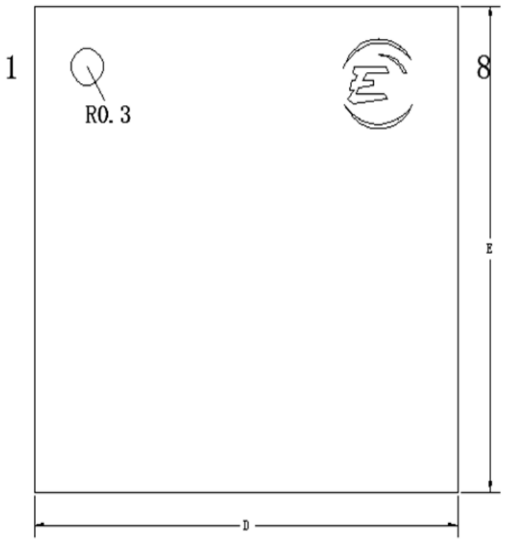
CorEnergy®

CE65H110DNDI

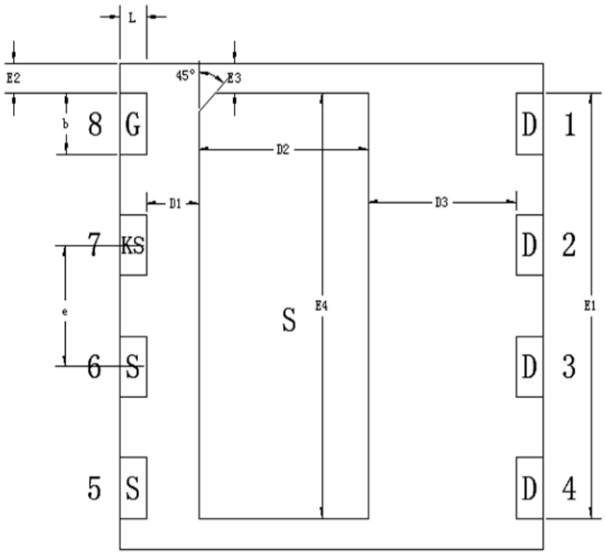
PACKAGE DIMENSIONS

DFN8x8-8L-1.10-A

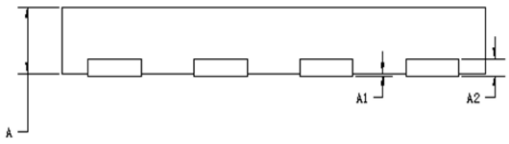
Top view



Bottom view



Side view(left/right)



Symbol	Min. (mm)	Mean. (mm)	Max. (mm)
A	1.05	1.10	1.15
A1	0	0.02	0.05
A2		0.203REF	
D	7.9	8	8.1
E	7.9	8	8.1
D1	0.9	1	1.1
D2	3.1	3.2	3.3
D3	2.7	2.8	2.9
E1	6.9	7	7.1
E2	0.4	0.5	0.6
E3	0.4	0.5	0.6
E4	6.9	7	7.1
e	1.9	2	2.1
b	0.9	1	1.1
L	0.4	0.5	0.6

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CE65H110DNDI

Revision history

Major changes since the last revision

Revision	Date	Description of changes
1.0	2022-02-28	Initial release
2.0	2023-10-30	Enrich dynamic specification curves
3.0	2023-12-25	Update dynamic parameters
4.0	2025-01-02	Optimize application platform testing